



**THE DATASHEET OF
SUD42N03-3M9P-GE3**



N-Channel 30 V (D-S) MOSFET

| PRODUCT SUMMARY | | | |
|---------------------|-----------------------------------|--------------------|-----------------------|
| V _{DS} (V) | R _{DS(on)} (Ω) | I _D (A) | Q _g (Typ.) |
| 30 | 0.0039 at V _{GS} = 10 V | 107 ^d | 67 |
| | 0.0045 at V _{GS} = 4.5 V | 103 ^d | |

FEATURES

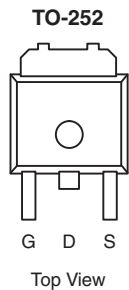
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



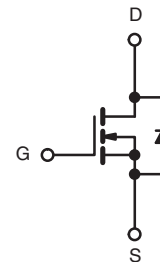
RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- DC/DC Converters
- Synchronous Buck Low Side



Drain Connected to Tab



N-Channel MOSFET

Ordering Information: SUD42N03-3m9P-GE3 (Lead (Pb)-free and Halogen-free)

| ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted) | | | | |
|---|-----------------------------------|--|-------------------|----|
| Parameter | Symbol | Limit | Unit | |
| Drain-Source Voltage | V _{DS} | 30 | V | |
| Gate-Source Voltage | V _{GS} | ± 20 | | |
| Continuous Drain Current | I _D | T _C = 25 °C (Silicon Limited) | 107 ^d | |
| | | T _C = 70 °C (Silicon Limited) | 85 ^d | |
| | | T _C = 25 °C (Package Limited) | 42 | |
| Pulsed Drain Current (t = 300 μs) | I _{DM} | 120 | A | |
| Avalanche Current | I _{AS} | 45 | | |
| Single Avalanche Energy ^a | E _{AS} | L = 0.1 mH | 101 | mJ |
| Maximum Power Dissipation ^a | | T _C = 25 °C | 73.5 ^b | |
| | | T _A = 25 °C ^c | 2.5 | W |
| Operating Junction and Storage Temperature Range | T _J , T _{stg} | - 55 to 150 | °C | |

| THERMAL RESISTANCE RATINGS | | | |
|--|-------------------|-------|------|
| Parameter | Symbol | Limit | Unit |
| Junction-to-Ambient (PCB Mount) ^c | R _{thJA} | 50 | °C/W |
| Junction-to-Case (Drain) | R _{thJC} | 1.7 | |

Notes:

a. Duty cycle ≤ 1 %.

b. See SOA curve for voltage derating.

c. When mounted on 1" square PCB (FR-4 material).

d. Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 42 A.

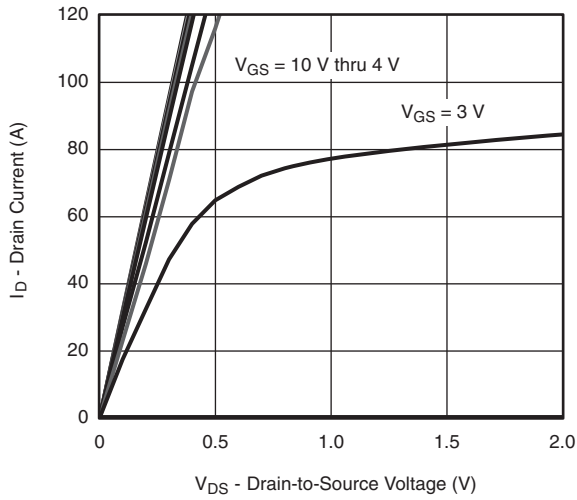
| SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | |
|---|---------------|---|------|--------|-----------|---------------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{DS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$ | 30 | | | V |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$ | 1 | | 2.5 | |
| Gate-Body Leakage | I_{GSS} | $V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$ | | | ± 250 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 30\text{ V}$, $V_{GS} = 0\text{ V}$ | | | 1 | μA |
| | | $V_{DS} = 30\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$ | | | 50 | |
| | | $V_{DS} = 30\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$ | | | 250 | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{DS} \geq 10\text{ V}$, $V_{GS} = 10\text{ V}$ | 50 | | | A |
| Drain-Source On-State Resistance ^a | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}$, $I_D = 22\text{ A}$ | | 0.0032 | 0.0039 | Ω |
| | | $V_{GS} = 4.5\text{ V}$, $I_D = 20\text{ A}$ | | 0.0037 | 0.0045 | |
| Forward Transconductance ^a | g_{fs} | $V_{DS} = 15\text{ V}$, $I_D = 20\text{ A}$ | | 110 | | S |
| Dynamic^b | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{ V}$, $V_{DS} = 15\text{ V}$, $f = 1\text{ MHz}$ | | 3535 | | μF |
| Output Capacitance | C_{oss} | | | 680 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 400 | | |
| Total Gate Charge ^c | Q_g | $V_{DS} = 15\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 20\text{ A}$ | | 67 | 100 | nC |
| Gate-Source Charge ^c | Q_{gs} | | | 10.5 | | |
| Gate-Drain Charge ^c | Q_{gd} | | | 12.2 | | |
| Gate Resistance | R_g | $f = 1\text{ MHz}$ | 0.3 | 1.4 | 2.8 | Ω |
| Turn-On Delay Time ^c | $t_{d(on)}$ | $V_{DD} = 15\text{ V}$, $R_L = 1.5\text{ }\Omega$ $I_D \cong 10\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\text{ }\Omega$ | | 11 | 20 | ns |
| Rise Time ^c | t_r | | | 10 | 20 | |
| Turn-Off Delay Time ^c | $t_{d(off)}$ | | | 35 | 53 | |
| Fall Time ^c | t_f | | | 10 | 20 | |
| Drain-Source Body Diode Ratings and Characteristics^b $T_C = 25\text{ }^\circ\text{C}$ | | | | | | |
| Continuous Current | I_S | | | | 42 | A |
| Pulsed Current | I_{SM} | | | | 120 | |
| Forward Voltage ^a | V_{SD} | $I_F = 10\text{ A}$, $V_{GS} = 0\text{ V}$ | | 0.83 | 1.5 | V |
| Reverse Recovery Time | t_{rr} | $I_F = 10\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ | | 41 | 62 | ns |
| Peak Reverse Recovery Current | $I_{RM(REC)}$ | | | 2 | 3 | A |
| Reverse Recovery Charge | Q_{rr} | | | 40 | 60 | nC |

Notes:

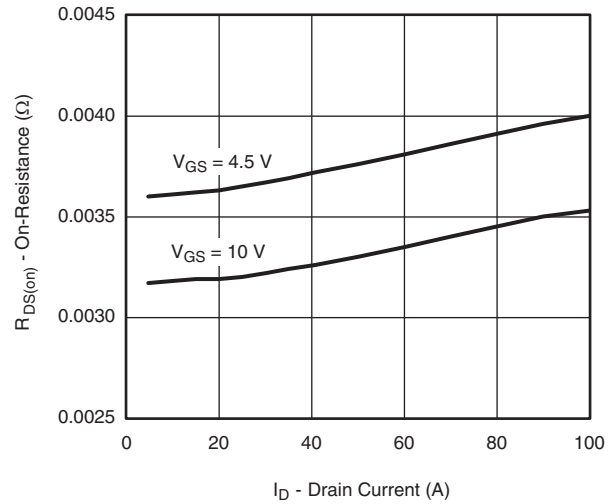
- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

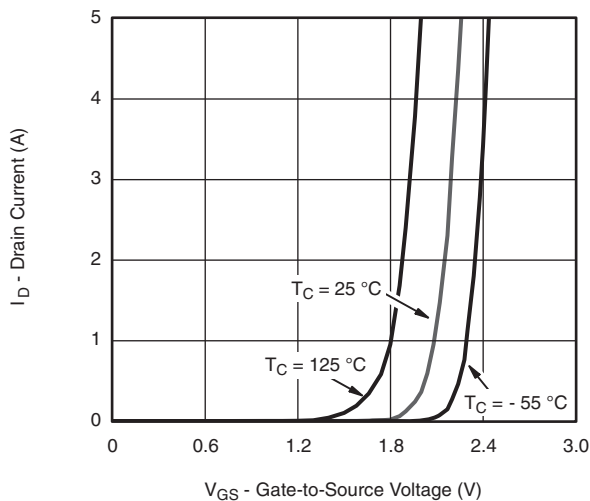
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



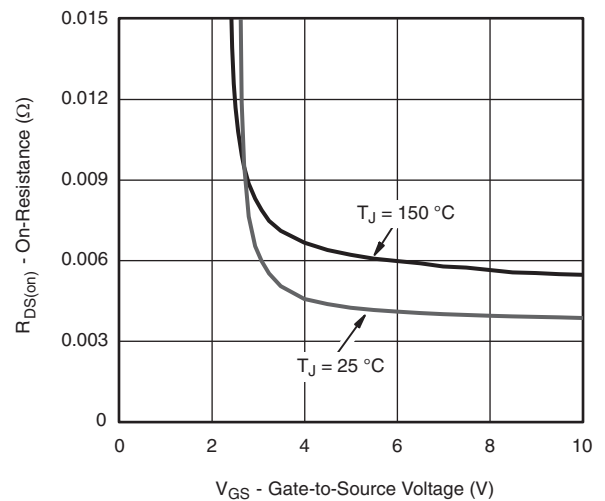
Output Characteristics



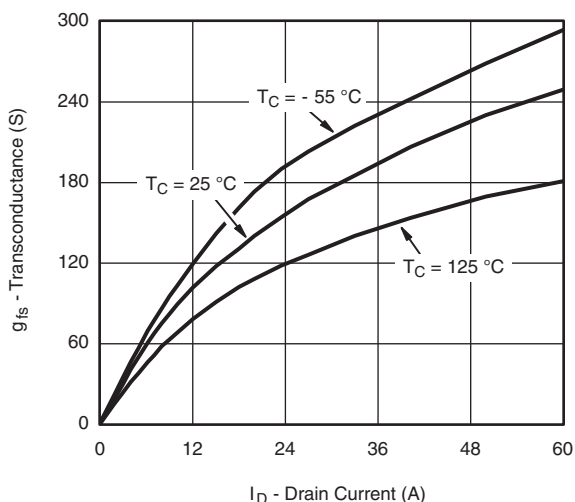
On-Resistance vs. Drain Current



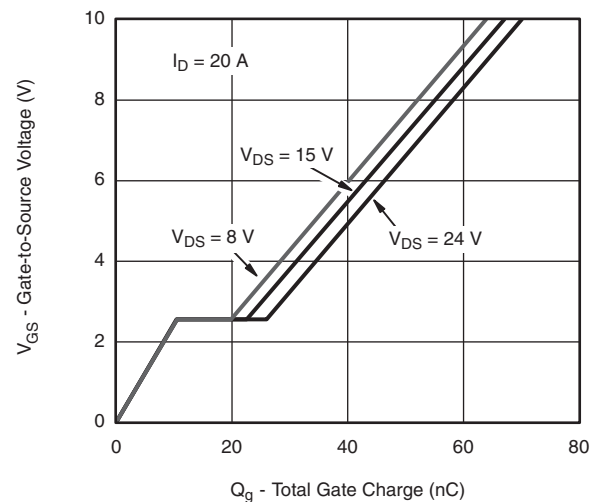
Transfer Characteristics



On-Resistance vs. Gate-to-Source Voltage

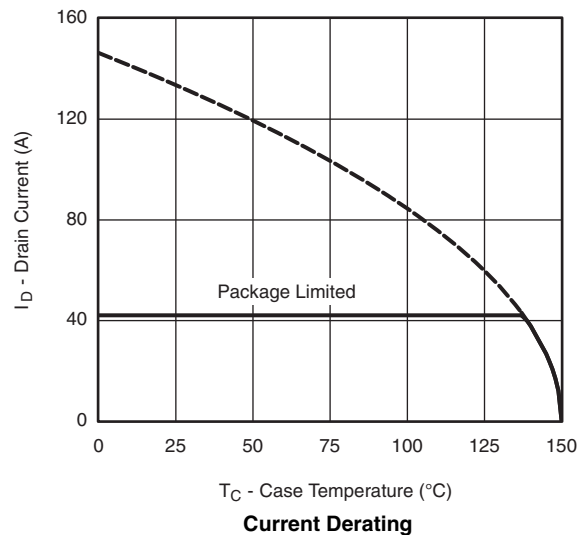
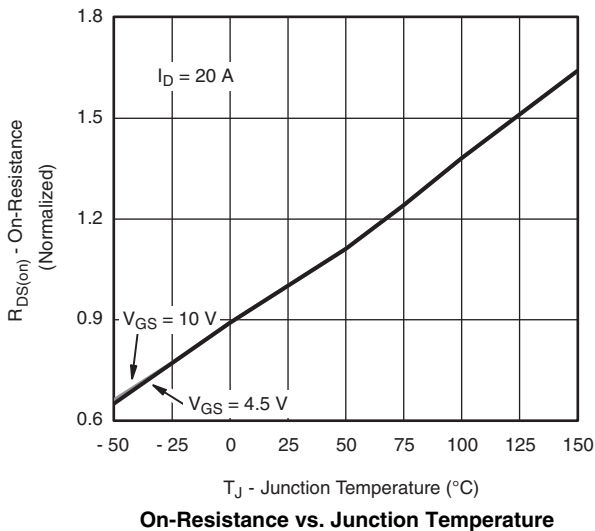
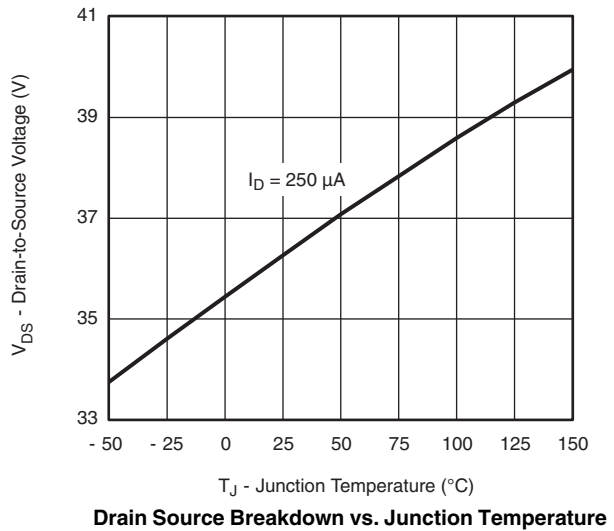
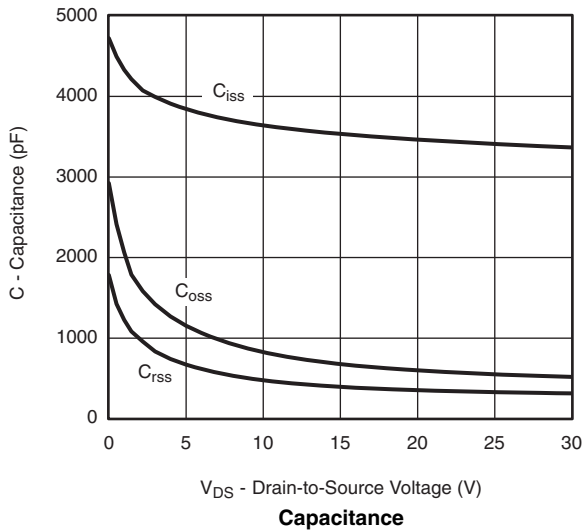
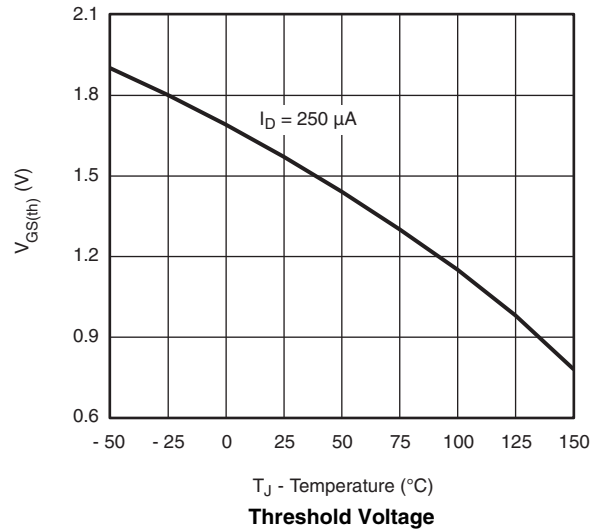
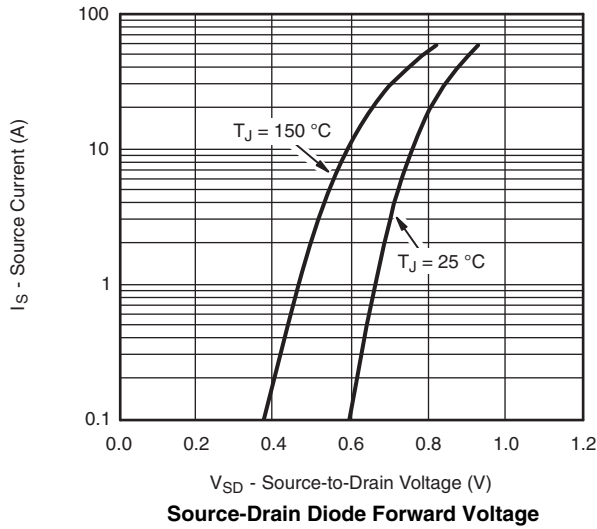


Transconductance

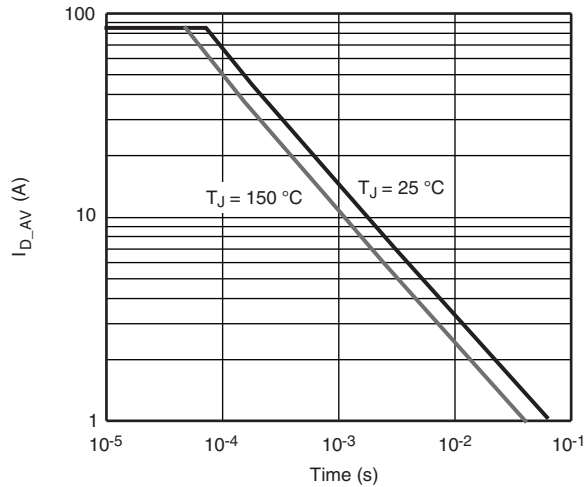


Gate Charge

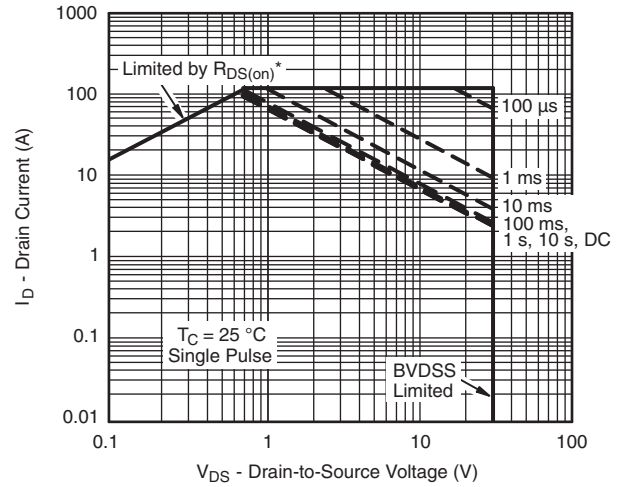
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



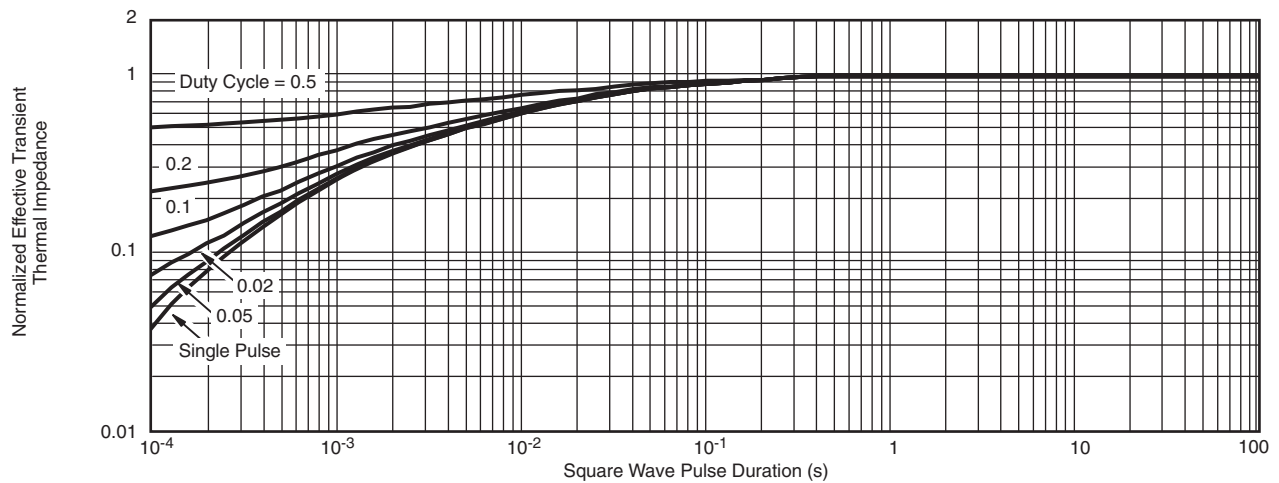
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Single Pulse Avalanche Current Capability vs. Time



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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TO-252AA Case Outline

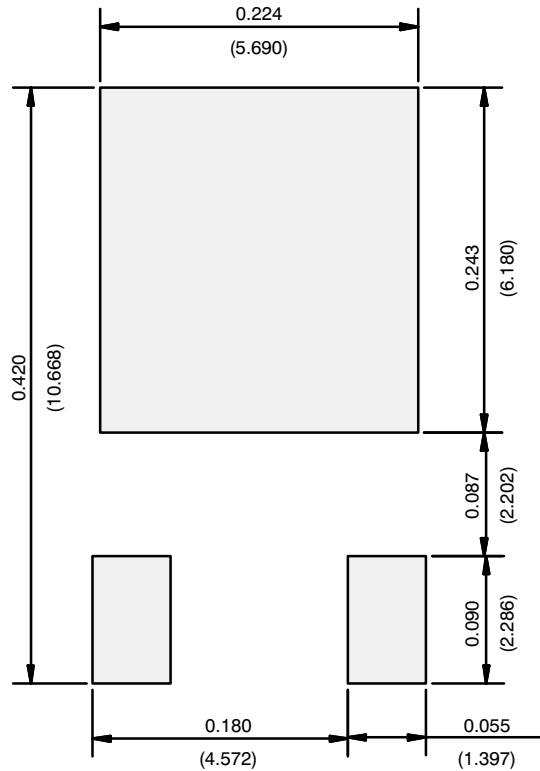


| DIM. | MILLIMETERS | | INCHES | |
|--|-------------|-------|-----------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A | 2.18 | 2.38 | 0.086 | 0.094 |
| A1 | - | 0.127 | - | 0.005 |
| b | 0.64 | 0.88 | 0.025 | 0.035 |
| b2 | 0.76 | 1.14 | 0.030 | 0.045 |
| b3 | 4.95 | 5.46 | 0.195 | 0.215 |
| C | 0.46 | 0.61 | 0.018 | 0.024 |
| C2 | 0.46 | 0.89 | 0.018 | 0.035 |
| D | 5.97 | 6.22 | 0.235 | 0.245 |
| D1 | 4.10 | - | 0.161 | - |
| E | 6.35 | 6.73 | 0.250 | 0.265 |
| E1 | 4.32 | - | 0.170 | - |
| H | 9.40 | 10.41 | 0.370 | 0.410 |
| e | 2.28 BSC | | 0.090 BSC | |
| e1 | 4.56 BSC | | 0.180 BSC | |
| L | 1.40 | 1.78 | 0.055 | 0.070 |
| L3 | 0.89 | 1.27 | 0.035 | 0.050 |
| L4 | - | 1.02 | - | 0.040 |
| L5 | 1.01 | 1.52 | 0.040 | 0.060 |
| ECN: T16-0236-Rev. P, 16-May-16 DWG: 5347 | | | | |

Notes

- Dimension L3 is for reference only.

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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